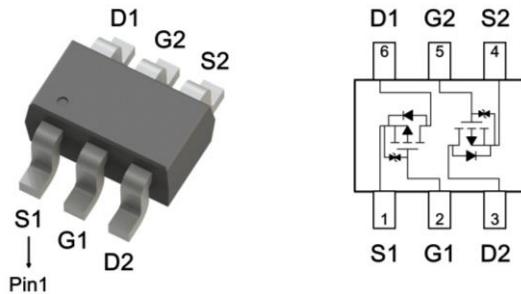


## Product Summary

$BV_{DSS}$	-60	V
$R_{DS(ON)}$ typ. @ $V_{GS}=-10V$ , $I_D=-0.2A$	3	$\Omega$
$R_{DS(ON)}$ typ. @ $V_{GS}=-4.5V$ , $I_D=-0.1A$	3.3	
$I_D$ @ $V_{GS}=-10V$ , $T_A=25^\circ C$	-0.24	A

## SOT-363



## Ordering Information

Device	Package	Shipping
MTB3K0B06KS6R-0-T1-G	SOT-363	3000pcs / Tape & Reel

0: Product rank, zero for no rank products.

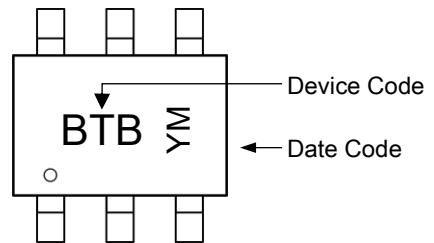
T1: Packing spec, T1 : 3000pcs / tape & reel, 7" reel

G: Environment friendly grade: S for RoHS compliant products, G for RoHS compliant and green compound products.

## Features

- Low Gate Charge
- Fast Switching Characteristic
- Pb-free lead plating and halogen-free
- ESD protected gate, typical 3kV (HBM)

## Marking



YM: Date Code Marking

Y: Year Code, the last digit of Christian year

M: Month Code

1: Jan	2: Feb	3: Mar	4: Apr	5: May	6: Jun
7: Jul	8: Aug	9: Sep	A: Oct	B: Nov	C: Dec

## Absolute Maximum Ratings ( $T_A=25^\circ C$ )

Parameter		Symbol	Value	Unit
Drain-Source Voltage		$V_{DS}$	-60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current @ $V_{GS}=-10V$ , $T_A=25^\circ C$	*a	$I_D$	-0.24	A
Continuous Drain Current @ $V_{GS}=-10V$ , $T_A=70^\circ C$	*a		-0.19	
Pulsed Drain Current	*b	$I_{DM}$	-0.96	
Continuous Body Diode Forward Current @ $T_A=25^\circ C$	*a	$I_S$	-0.24	
Pulsed Body Diode Forward Current @ $T_A=25^\circ C$	*a	$I_{SM}$	-0.96	
Total Power Dissipation	$T_A=25^\circ C$	$P_D$	0.5	W
	$T_A=70^\circ C$		0.3	
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55~+150	°C
Steady State Thermal Resistance, Junction-to-Ambient	*a	$R_{\theta JA}$	266	°C/W

Electrical Characteristics ( $T_A=25^\circ\text{C}$ , unless otherwise specified)

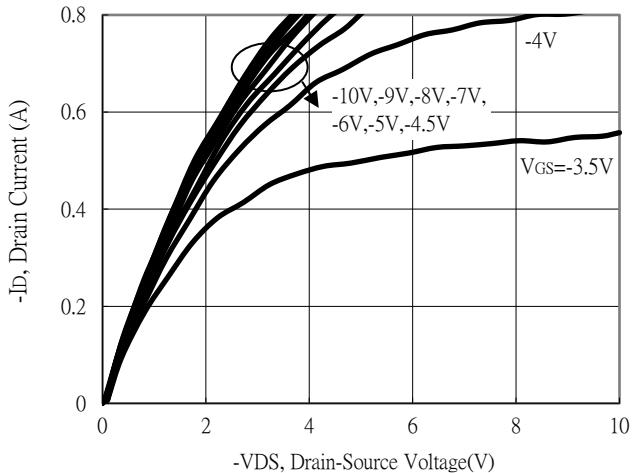
Symbol	Min.	Typ.	Max.	Unit	Test Conditions	
<b>Static</b>						
$\text{BV}_{\text{DSS}}$	-60	-	-	V	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$	
$\text{V}_{\text{GS}(\text{th})}$	-1	-	-2.5		$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=-250\mu\text{A}$	
$\text{G}_{\text{FS}}$	-	0.34	-	S	$\text{V}_{\text{DS}}=-10\text{V}, \text{I}_D=-0.1\text{A}$	
$\text{I}_{\text{GSS}}$	-	-	$\pm 10$		$\text{V}_{\text{GS}}=\pm 16\text{V}, \text{V}_{\text{DS}}=0\text{V}$	
$\text{I}_{\text{DSS}}$	-	-	-1	$\mu\text{A}$	$\text{V}_{\text{DS}}=-48\text{V}, \text{V}_{\text{GS}}=0\text{V}$	
$\text{R}_{\text{DS}(\text{ON})}$	-	3	4.4		$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-0.2\text{A}$	
	-	3.3	5	$\Omega$	$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-0.1\text{A}$	
<b>Dynamic</b>						
$\text{C}_{\text{iss}}$	-	35	-	pF		
$\text{C}_{\text{oss}}$	-	9	-		$\text{V}_{\text{DS}}=-30\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1\text{MHz}$	
$\text{C}_{\text{rss}}$	-	7	-	nC		
$\text{Q}_g$ *c,d	-	0.7	-		$\text{V}_{\text{DS}}=-30\text{V}, \text{I}_D=-0.2\text{A}, \text{V}_{\text{GS}}=-4.5\text{V}$	
$\text{Q}_g$ *c,d	-	1.5	-	nC		
$\text{Q}_{\text{gs}}$ *c,d	-	0.4	-		$\text{V}_{\text{DS}}=-30\text{V}, \text{I}_D=-0.2\text{A}, \text{V}_{\text{GS}}=-10\text{V}$	
$\text{Q}_{\text{gd}}$ *c,d	-	0.1	-	ns		
$t_{\text{d}(\text{ON})}$ *c,d	-	6.3	-			
$t_{\text{r}}$ *c,d	-	15	-	ns		
$t_{\text{d}(\text{OFF})}$ *c,d	-	27	-		$\text{V}_{\text{DS}}=-30\text{V}, \text{I}_D=-0.2\text{A}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_{\text{GS}}=6\Omega$	
$t_f$ *c,d	-	21	-	ns		
<b>Source-Drain Diode</b>						
$\text{V}_{\text{SD}}$ *d	-	-0.86	-1.2	V	$\text{I}_S=-0.2\text{A}, \text{V}_{\text{GS}}=0\text{V}$	
$t_{\text{rr}}$	-	11	-	ns		
$\text{Q}_{\text{rr}}$	-	4	-		$\text{I}_F=-0.2\text{A}, \text{di/dt}=100\text{A}/\mu\text{s}$	

## Note:

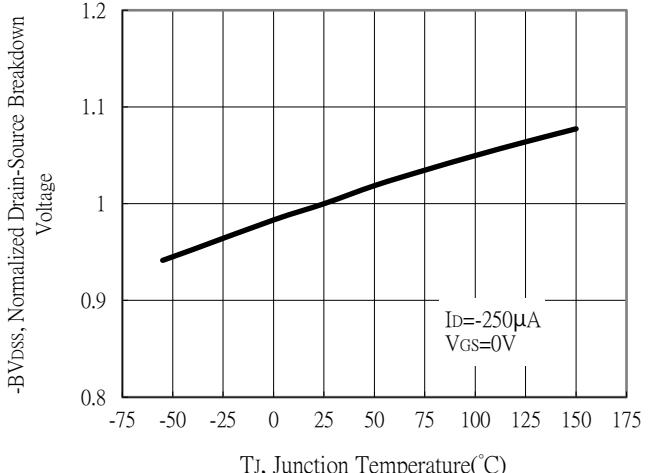
- \*a. The value of  $R_{\text{eJA}}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The power dissipation  $P_D$  is based on  $R_{\text{eJA}}$  and the maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.
- \*b. Repetitive rating, pulse width limited by junction temperature  $T_{\text{J}(\text{MAX})}=150^\circ\text{C}$ . Ratings are based on low frequency and low duty cycles to keep initial  $T_J=25^\circ\text{C}$ .
- \*c. Pulse Test : Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 2\%$ .
- \*d. Independent of operating temperature.

## Typical Characteristics

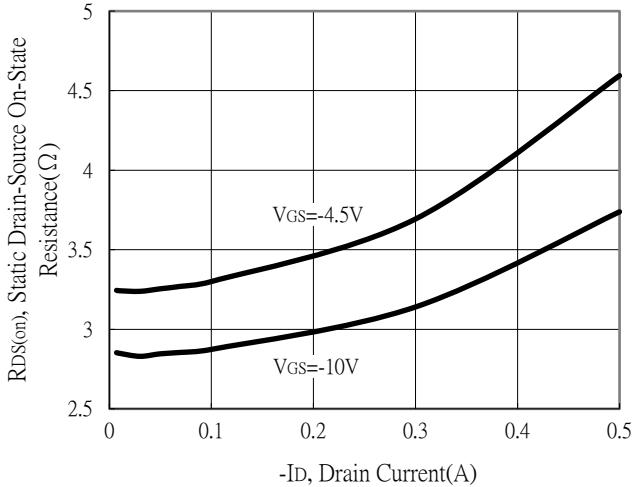
Typical Output Characteristics



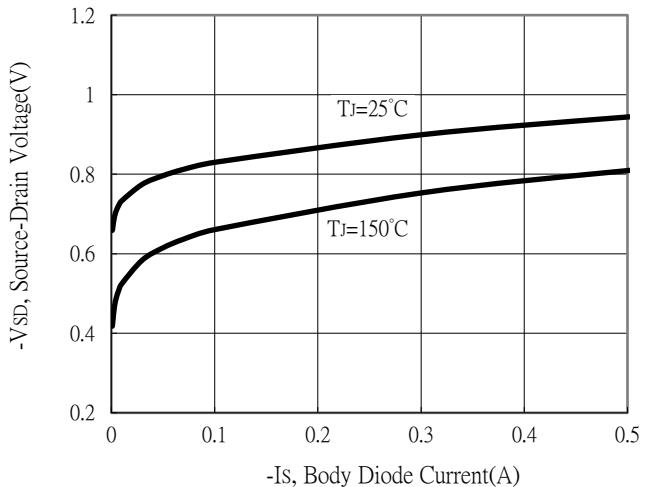
Breakdown Voltage vs Junction Temperature



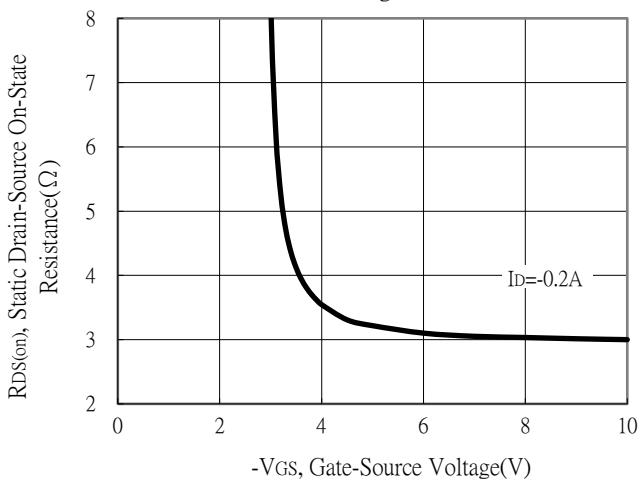
Static Drain-Source On-State resistance vs Drain Current



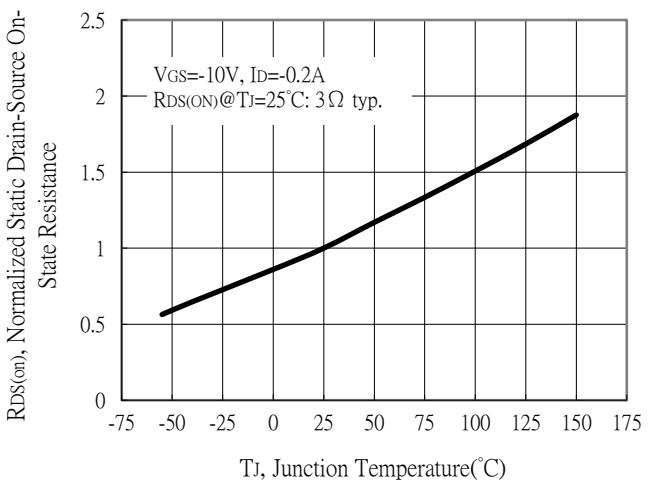
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

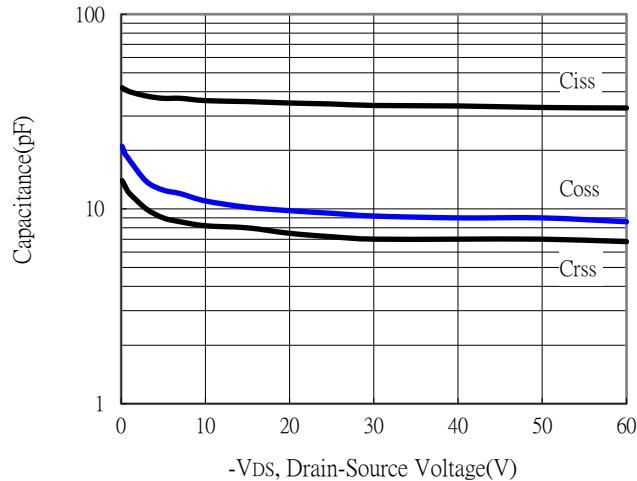


Drain-Source On-State Resistance vs Junction Temperature

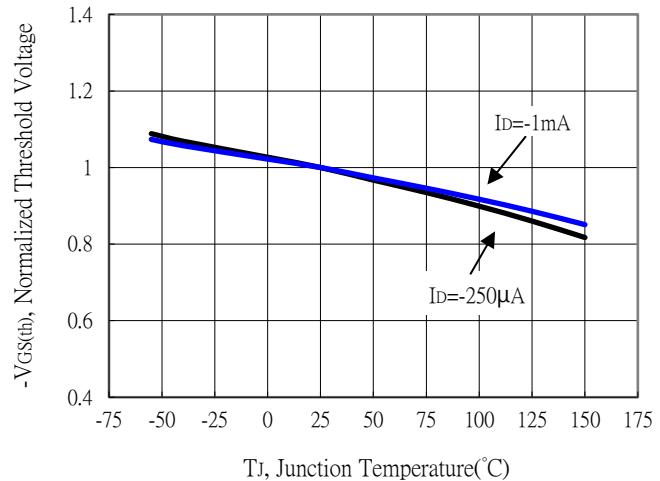


## Typical Characteristics

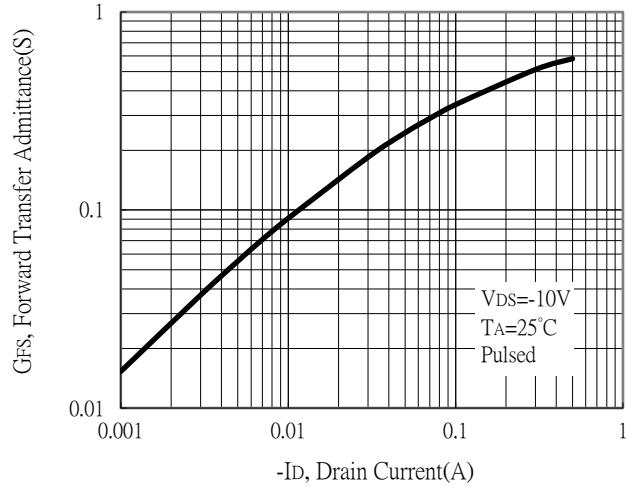
Capacitance vs Drain-to-Source Voltage



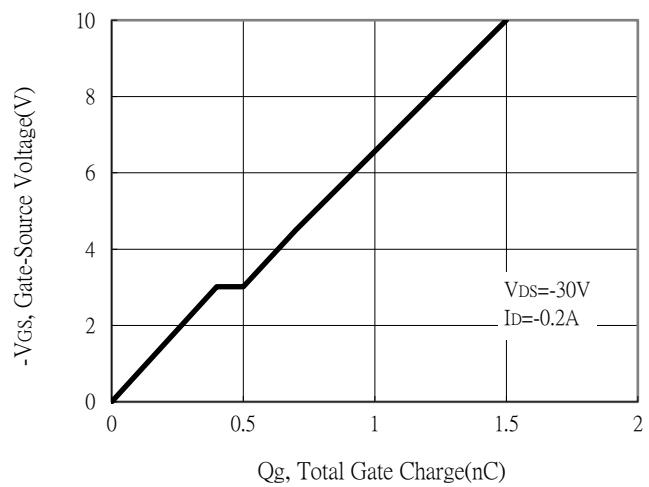
Threshold Voltage vs Junction Temperature



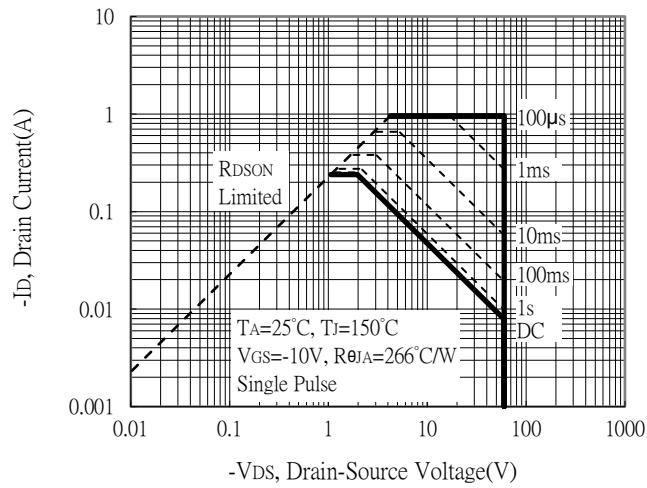
Forward Transfer Admittance vs Drain Current



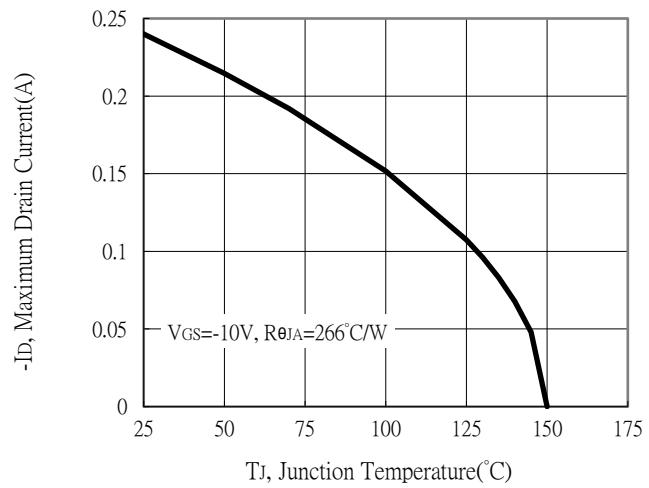
Gate Charge Characteristics



Maximum Safe Operating Area

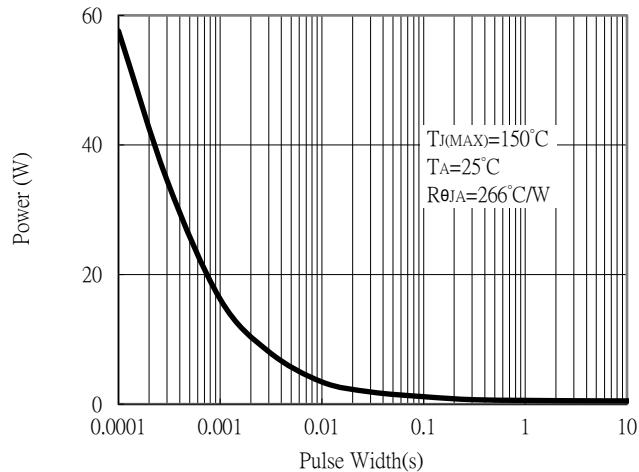


Maximum Drain Current vs Junction Temperature

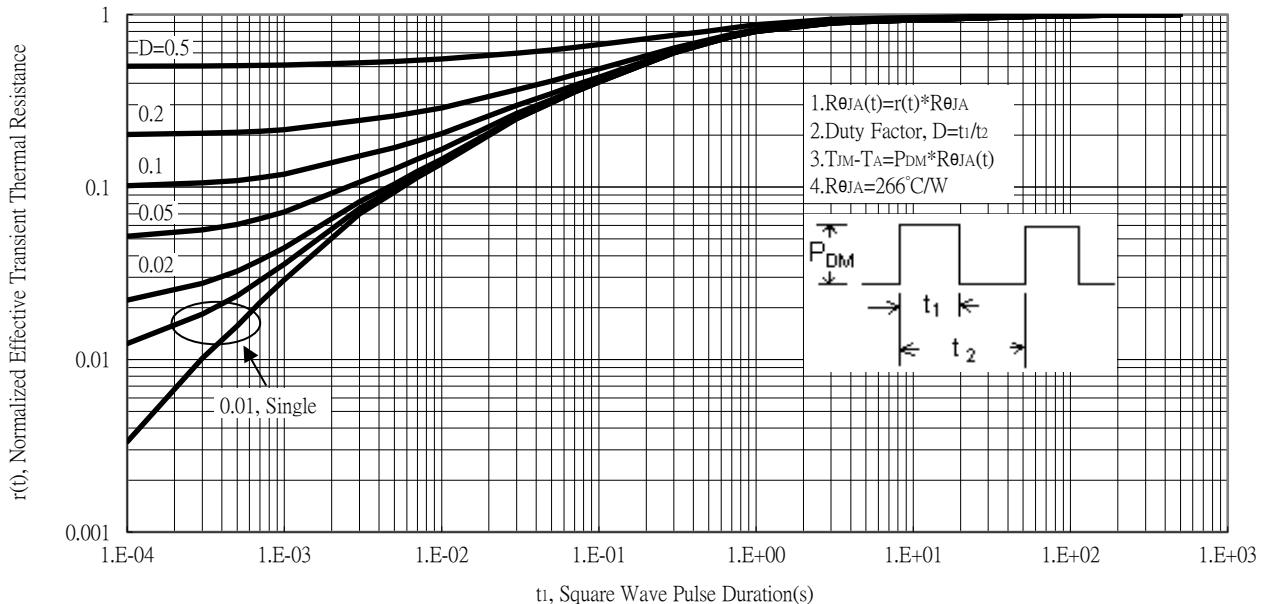


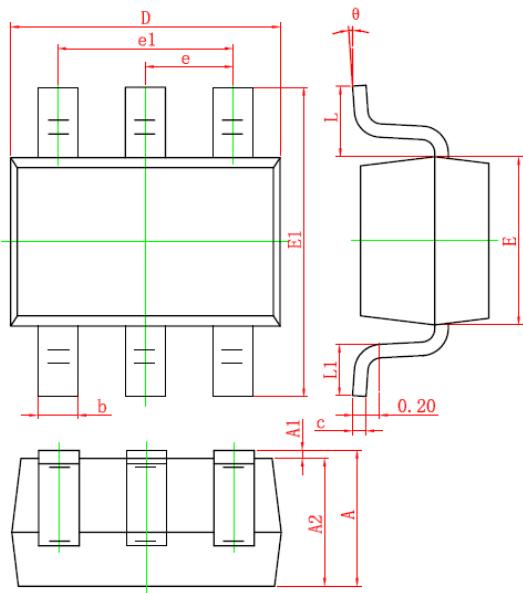
## Typical Characteristics

Single Pulse Power Rating, Junction to Ambient

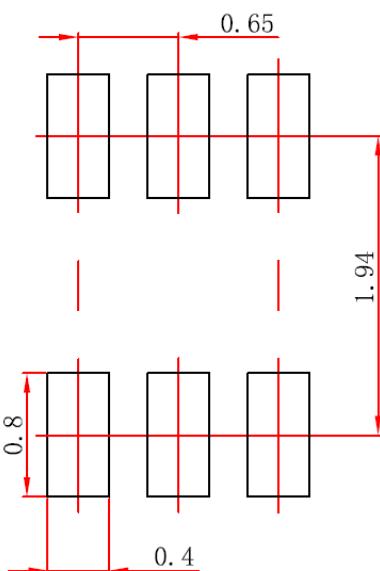


Transient Thermal Response Curves



**SOT-363 Dimension**


6-Lead SOT-363 Plastic Surface Mount Package  
CYS Package Code: S6R



Recommended Soldering Footprint

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.035	0.043	0.900	1.100	E1	0.085	0.096	2.150	2.450
A1	0.000	0.004	0.000	0.100	e	0.026	TYP.	0.650	TYP.
A2	0.035	0.039	0.900	1.000	e1	0.047	0.055	1.200	1.400
b	0.006	0.014	0.150	0.350	L	0.021	REF.	0.525	REF.
c	0.003	0.006	0.080	0.150	L1	0.010	0.018	0.260	0.460
D	0.079	0.087	2.000	2.200	θ	0°	8°	0°	8°
E	0.045	0.053	1.150	1.350					

**Note:**

- Controlling dimension: millimeters.
- Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
- If there is any question with packing specification or packing method, please contact your local CYStek sales office.

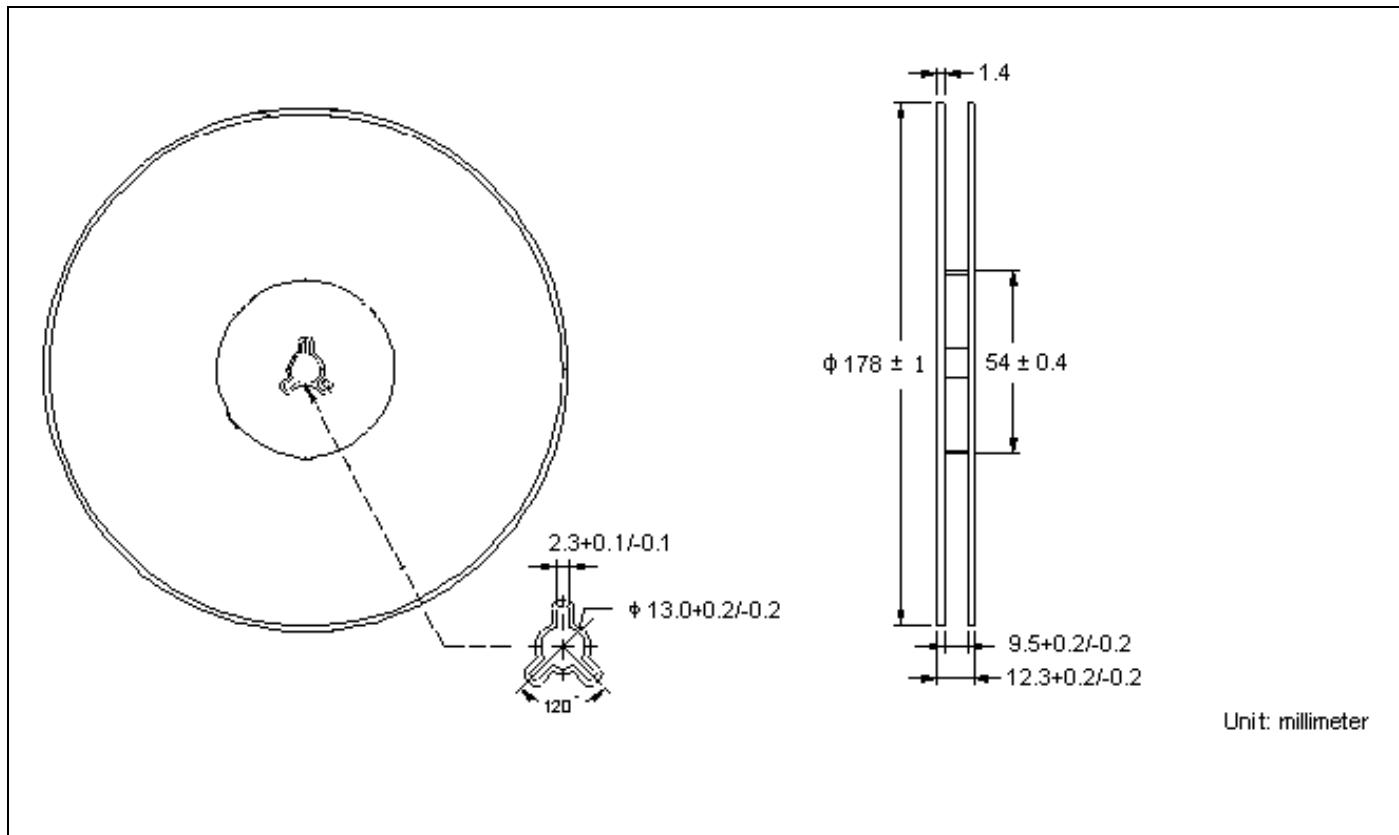
**Material:**

- Lead: pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

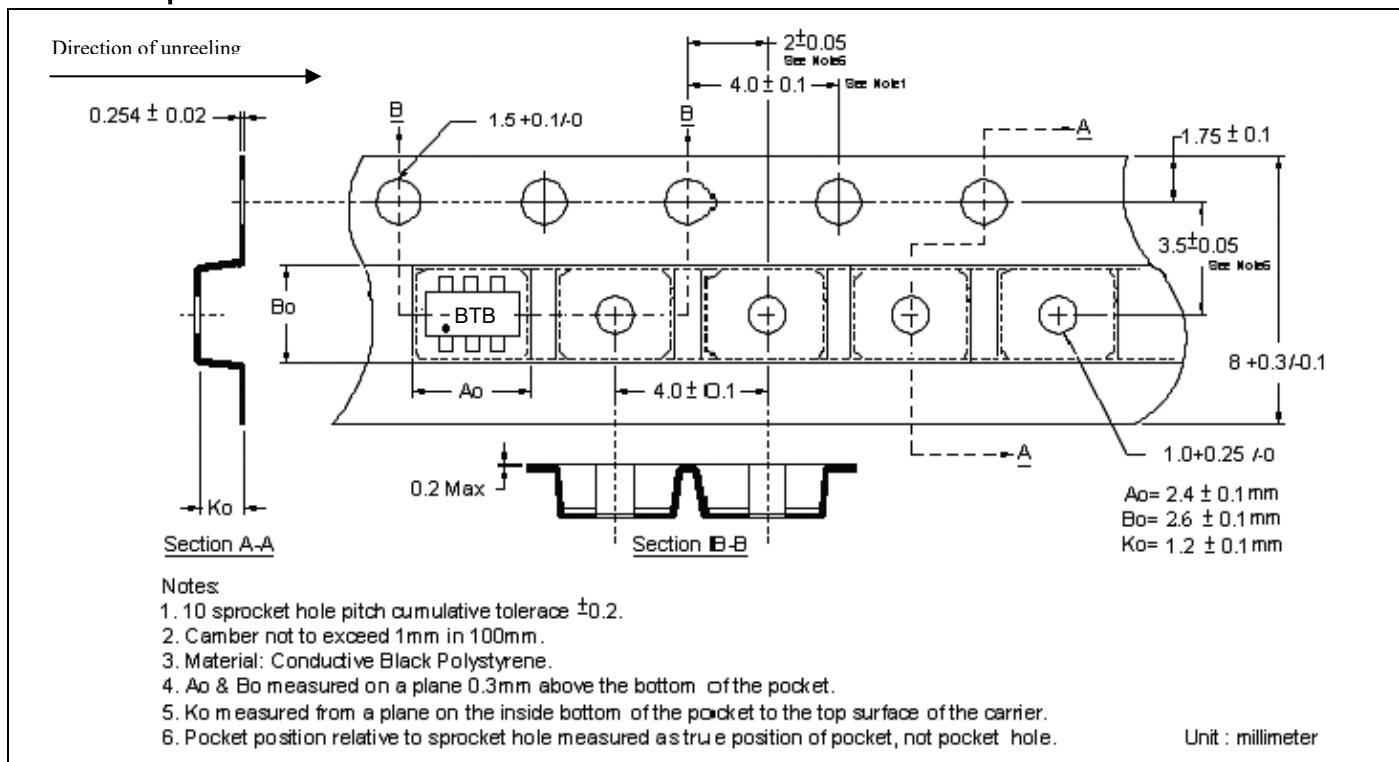
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## Reel Dimension



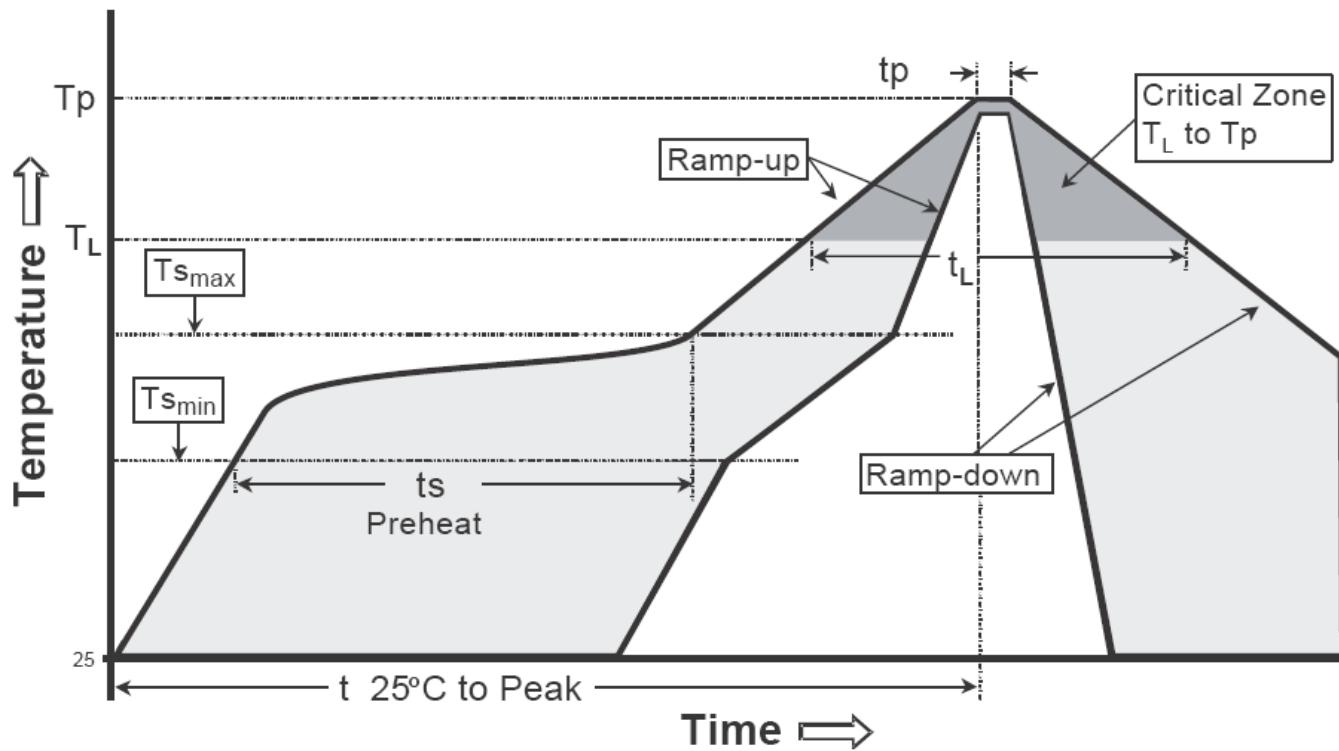
## Carrier Tape Dimension



## Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

## Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate ( $T_s$ max to $T_p$ )	3°C/second max.	3°C/second max.
Preheat -Temperature Min ( $T_s$ min) -Temperature Max ( $T_s$ max) -Time ( $t_s$ min to $t_s$ max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature ( $T_L$ ) -Time ( $t_L$ )	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature ( $T_p$ )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature ( $t_p$ )	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

**Note:**

- All temperatures refer to topside of the package, measured on the package body surface.